

2SD1472

Silicon NPN Epitaxial, Darlington

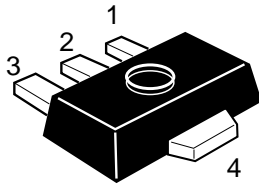
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Application

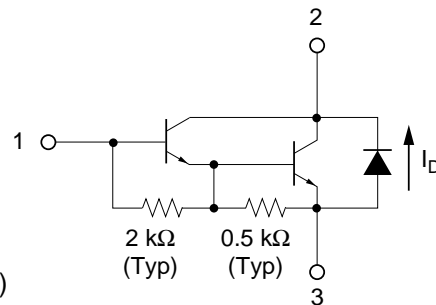
Low frequency power amplifier

Outline

UPAK



1. Base
2. Collector
3. Emitter
4. Collector (Flange)



Absolute Maximum Ratings (Ta = 25°C)

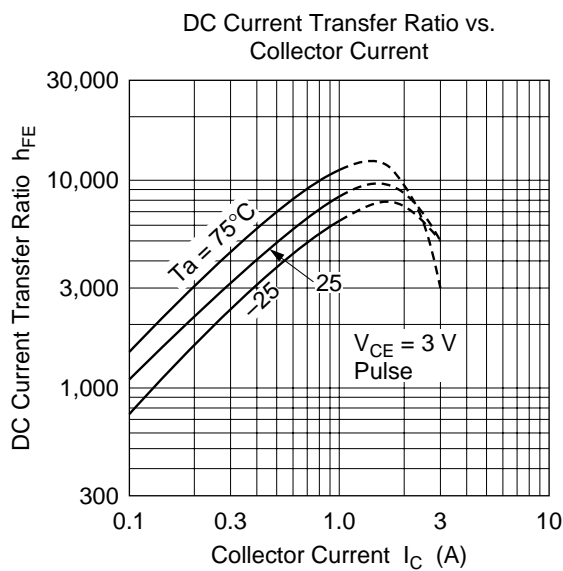
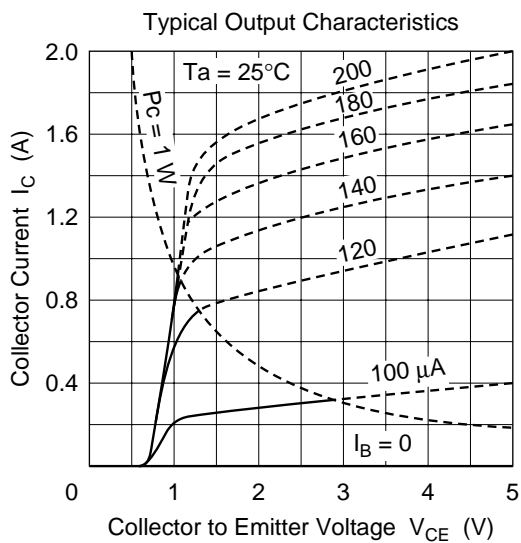
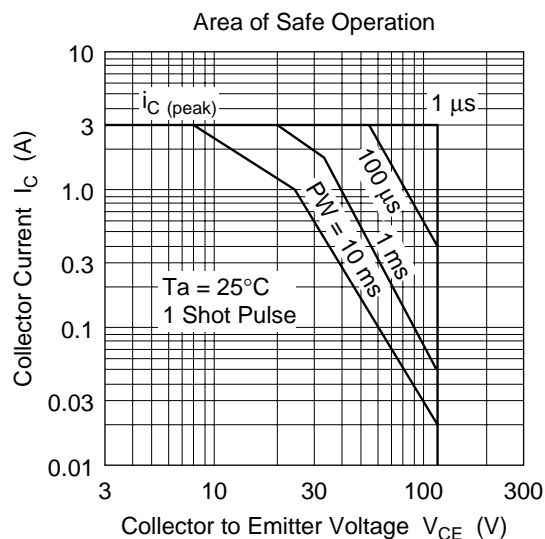
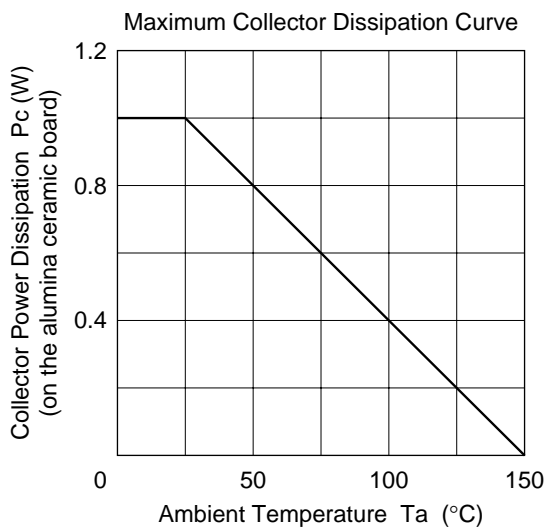
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	120	V
Collector to emitter voltage	V_{CEO}	120	V
Emitter to base voltage	V_{EBO}	7	V
Collector current	I_C	1.5	A
Collector peak current	$i_{C(peak)}^{*1}$	3.0	A
Collector power dissipation	P_C^{*2}	1.0	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C
E to C diode forward current	I_D	1.5	A

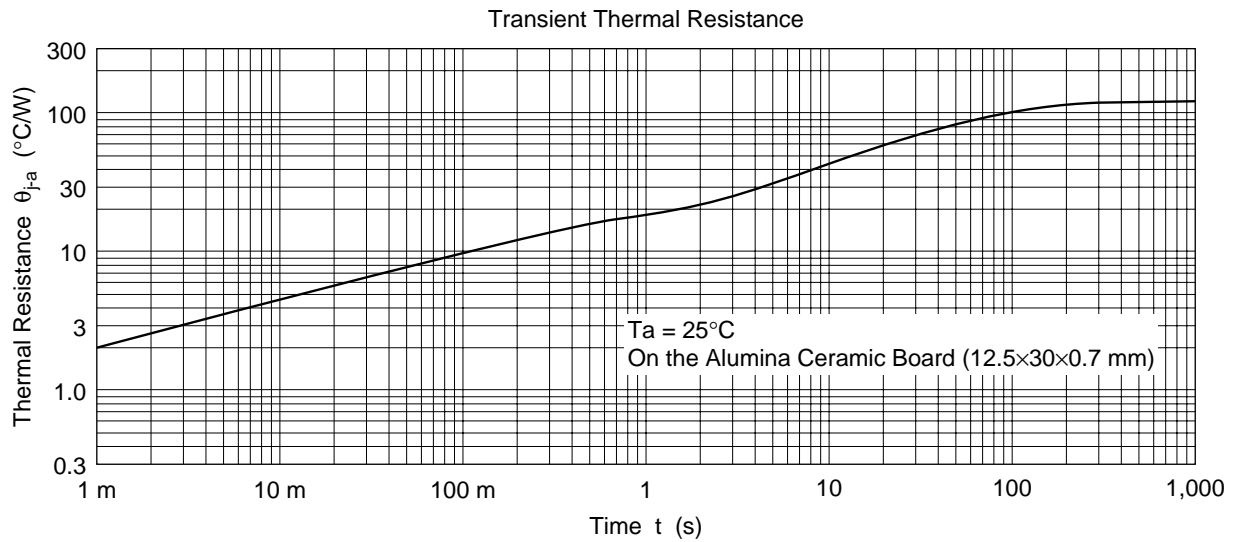
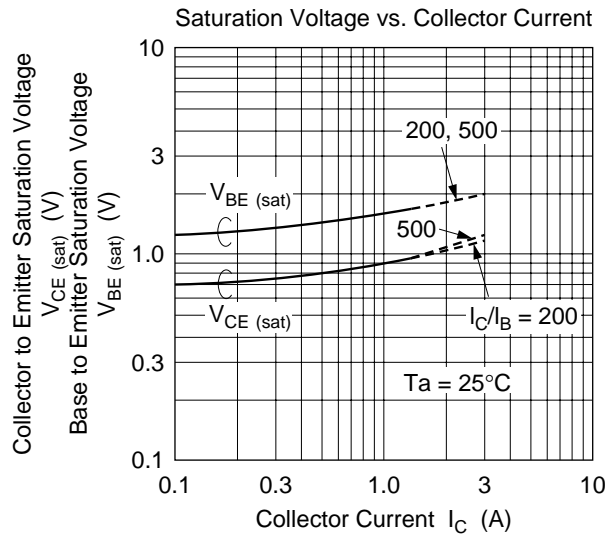
- Notes: 1. Pulse ≤ 10 ms, Duty cycle $\leq 20\%$
 2. Value on the alumina ceramic board (12.5 x 30 x 0.7 mm)

Electrical Characteristics (Ta = 25°C)

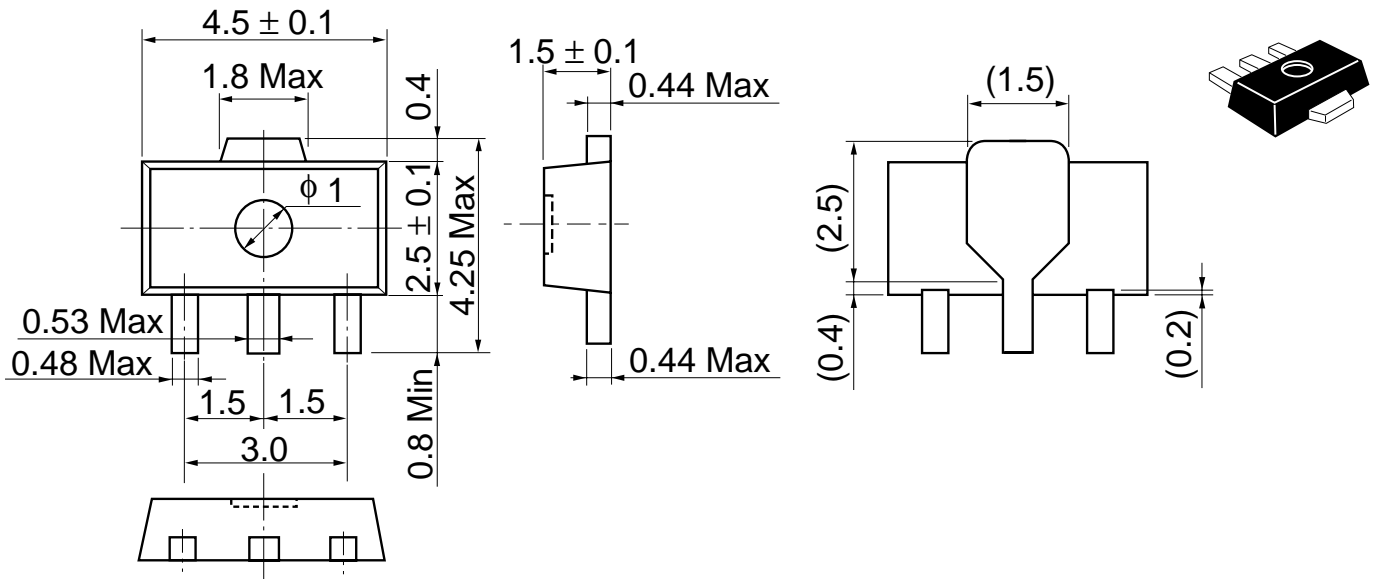
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	120	—	—	V	$I_C = 0.1$ mA, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	V	$I_C = 10$ mA, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 50$ mA, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	1.0	μ A	$V_{CB} = 100$ V, $I_E = 0$
	I_{CEO}	—	—	10	μ A	$V_{CE} = 100$ V, $R_{BE} = \infty$
DC current transfer ratio	h_{FE}	2000	—	30000		$V_{CE} = 3$ V, $I_C = 1$ A ^{*1}
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	1.5	V	$I_C = 1$ A, $I_B = 1$ mA ^{*1}
	$V_{CE(sat)2}$	—	—	2.0	V	$I_C = 1.5$ A, $I_B = 1.5$ mA ^{*1}
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	2.0	V	$I_C = 1$ A, $I_B = 1$ mA ^{*1}
	$V_{BE(sat)2}$	—	—	2.5	V	$I_C = 1.5$ A, $I_B = 1.5$ mA ^{*1}
E to C diode forward voltage	V_D	—	—	3.0	V	$I_D = 1.5$ A ^{*1}

- Notes: 1. Pulse test
 2. Marking is "CT".





Unit: mm



Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.050 g

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